



Attorney's Docket No. 42390P5783D

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:

Steven N. Towle

Application No.: 10/082,997

Filed: February 25, 2002

For: METHOD FOR IMPROVING THERMAL
STABILITY OF FLUORINATED AMORPHOUS
CARBON LOW DIELECTRIC
CONSTANT MATERIALS

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

Examiner: McDonald, Rodney Glenn

Art Unit: 1753

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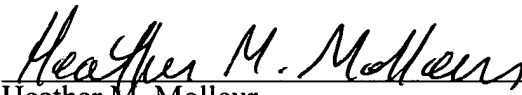
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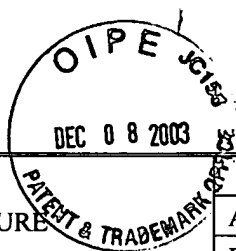
Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: 12/3, 2003


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Substitute for Form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known	
			Application Number	10/082,997
			Filing Date	February 25, 2002
			First Named Inventor:	Steven N. Towle
			Art Unit	1753
			Examiner Name	McDonald, Rodney Glenn
Sheet	1	of 1	Attorney Docket Number	42390P5783D

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		ANNEN, A., ET AL., Erosion of amorphous hydrogenated boron-carbon thin films, Journal of Nuclear Materials 231 (1996) pgs. 151-154, © 1996 Elsevier Science, B.V.	
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by helicon plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (20) 13 May 1996, pgs. 2864-2866, © American Institute of Physics.	
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, J. Appl. Phys. 78 (2), 15 July 1995, pgs. 1370-1372, © 1995 American Institute of Physics.	
		ENDO, KAZUHIKO, ET AL., Nitrogen doped fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (25), 17 June 1996, pgs. 3656-3658 © 1996 American Institute of Physics.	
		MATSUBARA, Y., ET AL., Low-k Fluorinated Amorphous Carbon Interlayer Technology for Quarter Micron Devices, ULSI Device Development Labs, *Microelectronic Res. Labs., **VLSI Manufacturing Engineering Division, NEC Corporation, 1120 Shimokuzawa, Sagami-hara, Kanagawa, 229, Japan, 4 pages, No Date.	
		SHARAPOV, V.M., ET AL., Erosion of a-B/C : H films under deuterium plasma irradiation, Journal of Nuclear Materials 220-222 (1995) 930-933, pgs. 930-933, © 1995 Elsevier Science B.V.	
		YAMAKI, T., ET AL., Thermal desorption spectroscopy of boron/carbon films after keV deuterium irradiation, Journal of Nuclear Materials 217 (1994) 154-160, pgs. 154-160, © 1994 Elsevier Science B.V.	

Examiner Signature		Date Considered	
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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